AT0P6SN030EQNC-Q1

N-Channel Enhancement Mode MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
30V	420mΩ@4.5V	0.6A
	540mΩ@2.5V	

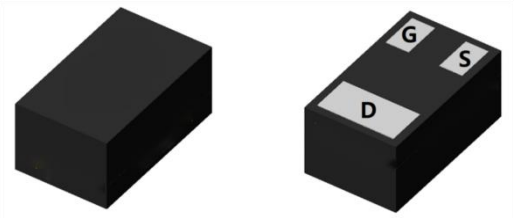
Feature

- N-Channel switch with low $R_{DS(on)}$
- Operated at low logic level gate drive
- ESD protected
- Suffix “-Q1” for AEC-Q101

Application

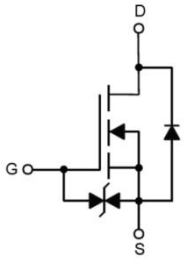
- N-channel enhancement mode effect transistor
- Switching application

Package



DFN1006-3L

Circuit diagram



Marking

KM

Absolute maximum ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current[1)]	I_D	0.6	A
Pulsed Drain Current (t_p =10μs)	I_{DM}	1.8	A
Single Pulse Avalanche Energy[3)]	E_{AS}	2	mJ
Power Dissipation[1)]	P_D	0.15	W
Thermal Resistance Junction to Ambient[1)]	$R_{\theta JA}$	833	℃/W
Operating Junction Temperature	T_J	-55 ~ +150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} =0V, I_D =250μA	30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =30V, V_{GS} =0V			1	μA
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±10V			±3	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.5	0.95	1.5	V
Drain-source on-resistance[2)]	$R_{DS(on)}$	V_{GS} =4.5V, I_D =0.6A		335	420	mΩ
		V_{GS} =2.5V, I_D =0.3A		404	540	
Dynamic characteristics[4)]						
Input Capacitance	C_{iss}	V_{DS} =10V, V_{GS} =0V, f =1MHz		73		pF
Output Capacitance	C_{oss}			29		
Reverse Transfer Capacitance	C_{rss}			16		
Total Gate Charge	Q_g	V_{DS} =15V, V_{GS} =4.5V, I_D =0.8A		2.23		nC
Gate-Source Charge	Q_{gs}			0.63		
Gate-Drain Charge	Q_{gd}			0.38		
Turn-on delay time	$t_{d(on)}$	V_{DS} =15V, V_{GS} =4.5V, I_D =0.7A R_G =51Ω		5		nS
Turn-on rise time	t_r			8.2		
Turn-off delay time	$t_{d(off)}$			23		
Turn-off fall time	t_f			41		
Source-Drain Diode characteristics						
Diode Forward Current	I_S				0.6	A
Diode Forward voltage[2)]	V_{SD}	V_{GS} =0V, I_S =0.6A			1.2	V

Notes:

1) The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2) The data tested by pulsed, pulse width ≤300μs, duty cycle ≤2%.

3) The EAS data shows Max. rating. The test condition is V_{DD} = 15V, V_{GS} = 6V, L =10mH.

4) Guaranteed by design, not subject to production testing.

Typical Characteristics

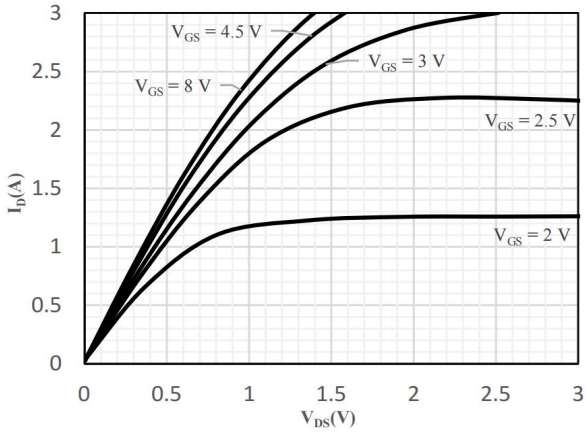


Fig 1 Output Characteristics

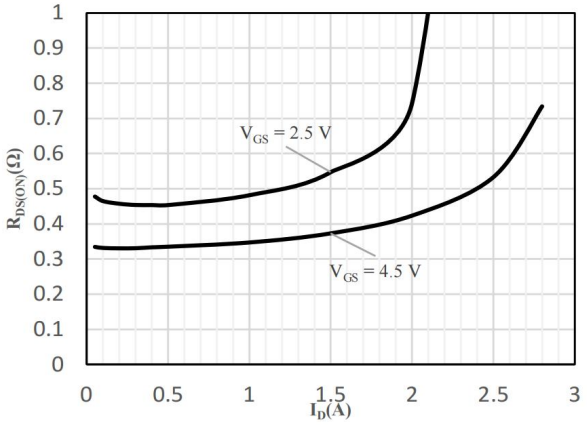


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

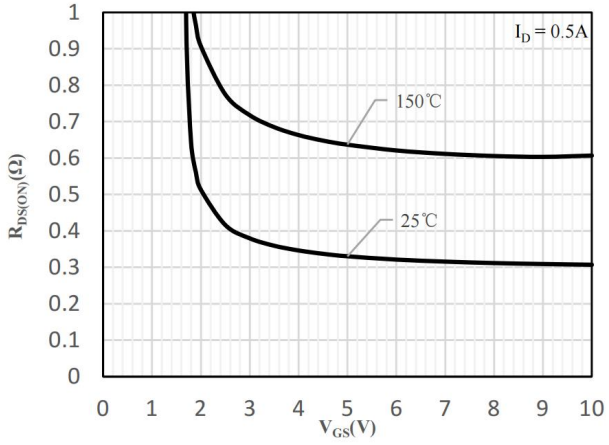


Fig 3 On-Resistance vs. Gate-Source Voltage

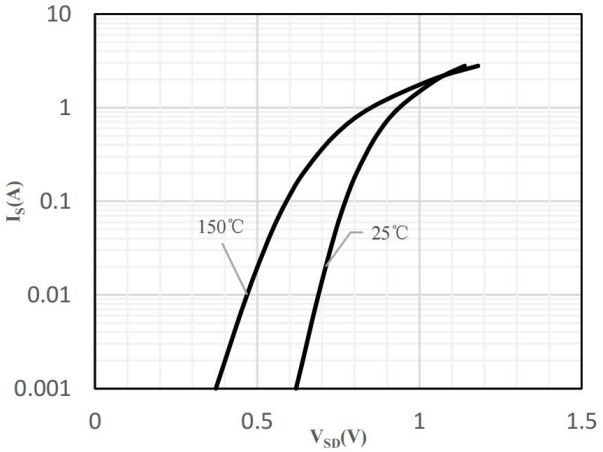


Fig 4 Body-Diode Characteristics

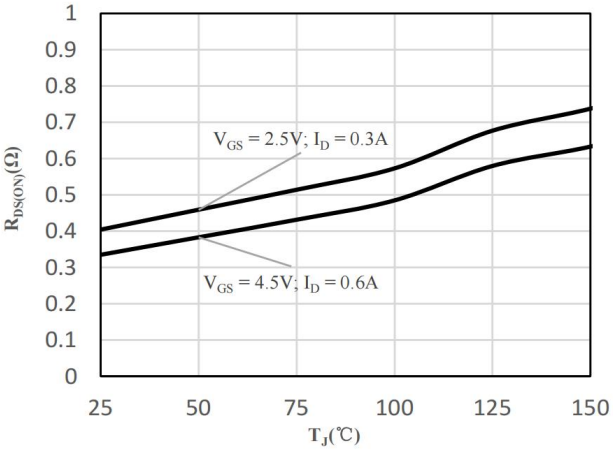


Fig 5 On-Resistance vs. Junction Temperature

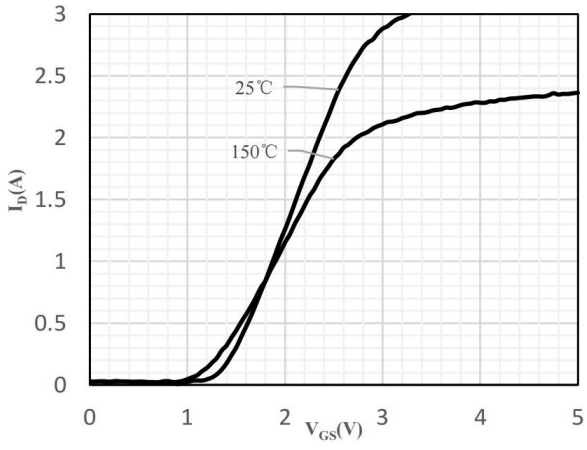


Fig 6 Transfer Characteristics

Typical Characteristics

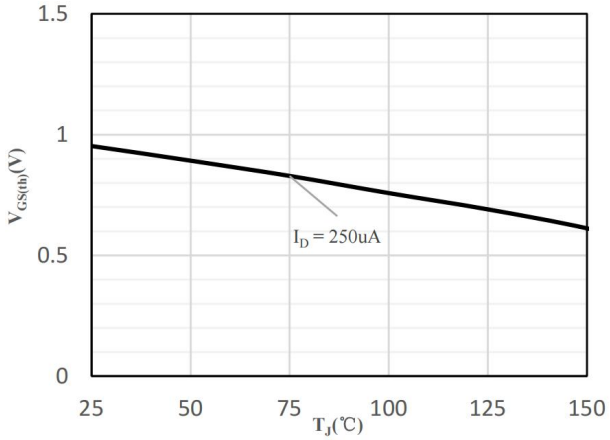


Fig 7 $V_{GS(th)}$ vs. Junction Temperature

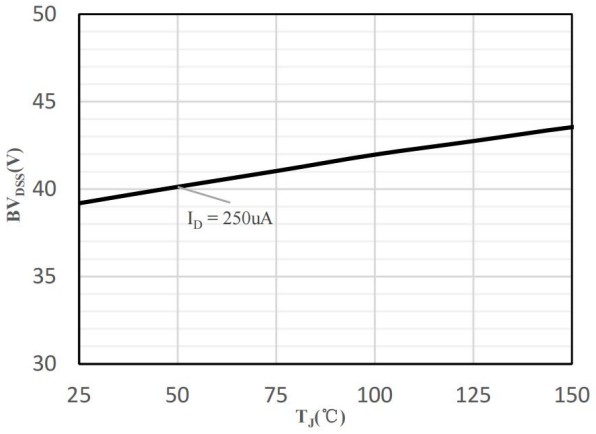


Fig 8 Breakdown Voltage vs. Junction Temperature

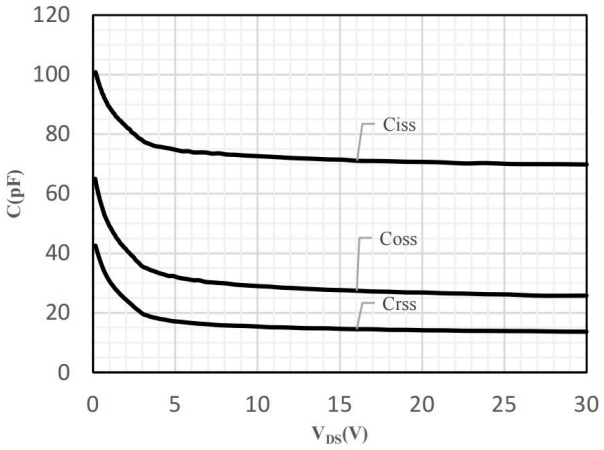


Fig 9 Capacitance Characteristics

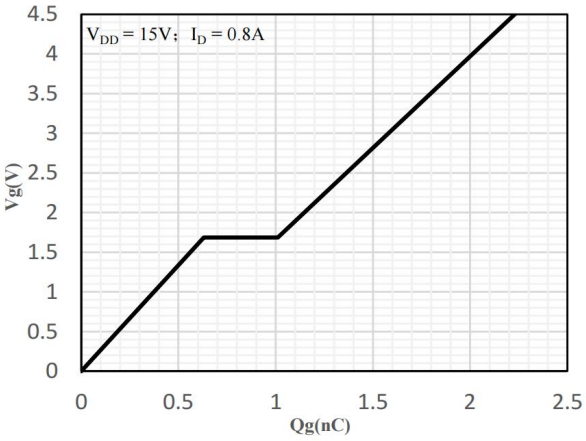
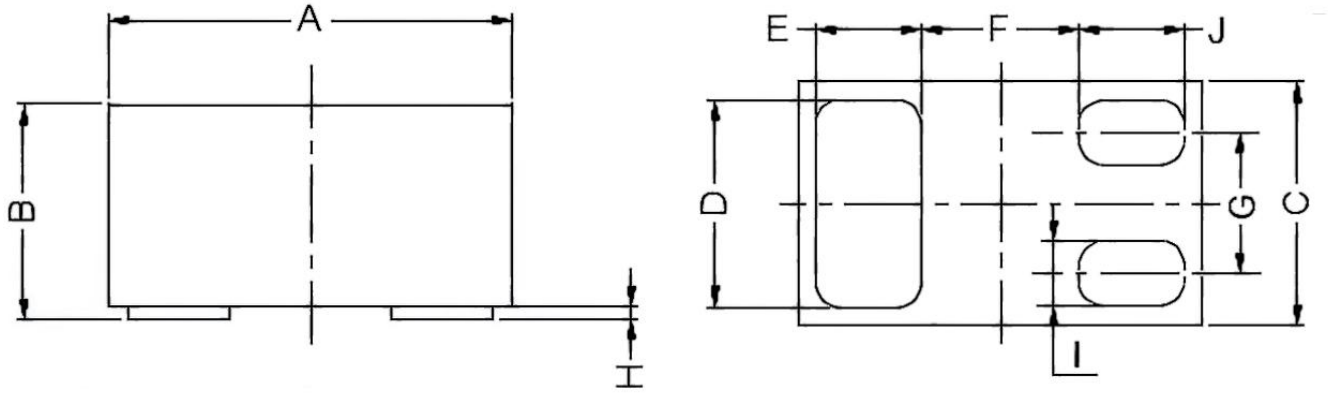


Fig 10 Gate-Charge Characteristics

DFN1006-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.950	1.075	0.037	0.042
B	0.470	0.530	0.019	0.021
C	0.550	0.675	0.022	0.027
D	0.450	0.550	0.018	0.022
E/J	0.200	0.300	0.008	0.012
F	0.400 BSC		0.016 BSC	
G	0.350 BSC		0.014 BSC	
H	0.000	0.050	0.000	0.002
I	0.100	0.200	0.004	0.008